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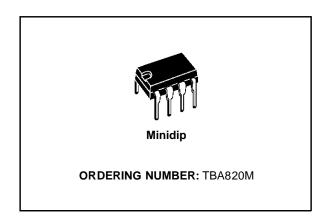
# **TBA820M**

# 1.2W AUDIO AMPLIFIER

#### **DESCRIPTION**

The TBA820M is a monolithic integrated audio amplifier in a 8 lead dual in-line plastic package. It is intended for use as low frequency class B power amplifier with wide range of supply voltage: 3 to 16V, in portable radios, cassette recorders and players etc. Main features are: minimum working supply voltage of 3V, low quiescent current, low number of external components, good ripple rejection, no cross-over distortion, low power dissipation.

Output power:  $P_0$  = 2W at 12V/8 $\Omega$ , 1.6W at 9V/4 $\Omega$  and 1.2W at 9V/8 $\Omega$ .



#### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
Vs	Supply voltage	16	V
Io	Output peak current	1.5	Α
P <sub>tot</sub>	Power dissipation at T <sub>amb</sub> = 50°C	1	W
T <sub>stg</sub> , T <sub>j</sub>	Storage and junction temperature	-40 to 150	°C

#### **TEST AND APPLICATION CIRCUITS**

Figure 1. Circuit diagram with load connected to the supply voltage

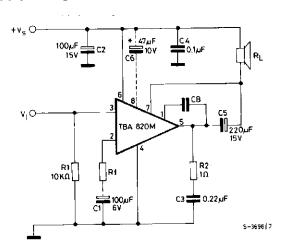
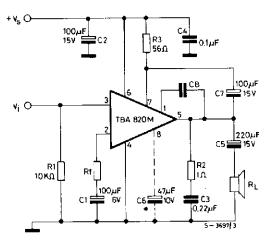


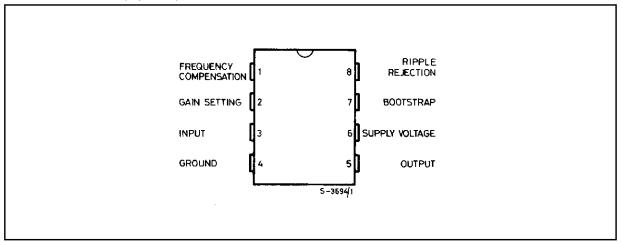
Figure 2. Circuit diagram with load connected to ground



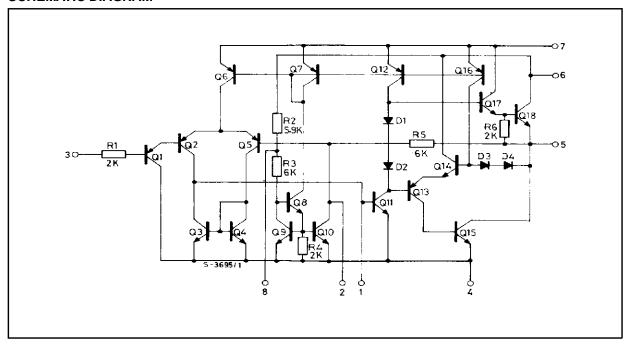
\* Capacitor C6 must be used when high ripple rejection is requested.

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## PIN CONNECTION (top view)



#### **SCHEMATIC DIAGRAM**



#### THERMAL DATA

Symbol	Symbol Parameter		Unit
R <sub>th-j-amb</sub>	Thermal resistance junction-ambient max	100	°C/W



# **ELECTRICAL CHARACTERISTICS** (Refer to the test circuits Vs = 9V, $T_{amb} = 25$ °C unless otherwise specified)

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
Vs	Supply voltage			3		16	V
Vo	Quiescent output voltage (pin 5)			4	4.5	5	V
I <sub>d</sub>	Quiescent drain current				4	12	mA
l <sub>b</sub>	Bias current (pin 3)				0.1		μА
Po	Output power	$\begin{aligned} &d = 10\% \\ &R_f = 120\Omega \\ &V_S = 12V \\ &V_S = 9V \\ &V_S = 9V \\ &V_S = 6V \\ &V_S = 3.5V \end{aligned}$	$f = 1 \text{ kHz}$ $R_L = 8\Omega$ $R_L = 4\Omega$ $R_L = 8\Omega$ $R_L = 4\Omega$ $R_L = 4\Omega$ $R_L = 4\Omega$	0.9	2 1.6 1.2 0.75 0.25		W W W W
Ri	Input resistance (pin 3)	f = 1 kHz			5		МΩ
В	Frequency response (-3 dB)	$R_L = 8\Omega$ $C_5 = 1000 \ \mu F$ $R_f = 120\Omega$	C <sub>B</sub> = 680 pF	25 to 7,000		Hz	
			C <sub>B</sub> = 220 pF	25 to 20,000			
d	Distortion	P <sub>o</sub> = 500 mW	$R_f = 33\Omega$		0.8		0/
		$R_L = 8\Omega$ f = 1 kHz	$R_f = 120\Omega$		0.4		%
Gv	Voltage gain (open loop)	f = 1 kHz	$R_L = 8\Omega$		75		dB
Gv	Voltage gain (closed loop)	$R_L = 8\Omega$	$R_f = 33\Omega$		45		dB
		f = 1 kHz	$R_f = 120\Omega$		34		, GD
e <sub>N</sub>	Input noise voltage (*)				3		μV
iΝ	Input noise current (*)				0.4		nA
S+N	Signal to noise ratio (*)	$P_o = 1.2W$ $R_L = 8\Omega$ $G_v = 34 \text{ dB}$	R1 = 10KΩ		80		dB
N			R1 = 50 kΩ		70		ub
SVR	Supply voltage rejection (test circuit of fig. 2)	$R_L = 8\Omega$ $f_{(ripple)} = 100 \text{ Hz}$ $C6 = 47 \mu\text{F}$ $R_f = 120\Omega$			42		dB

(\*) B = 22 Hz to 22 KHz

Figure 3. Output power vs. supply voltage

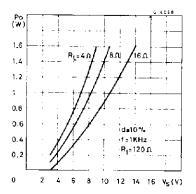


Figure 4. Harmonic distortion vs. output power

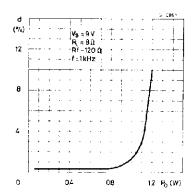


Figure 5. Power dissipation and efficiency vs. output power

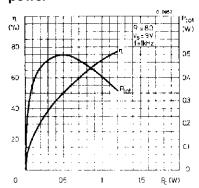


Figure 6. Maximum power dissipation (sine wave operation)

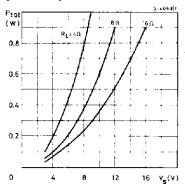


Figure 7. Suggested value of CB vs. Rf

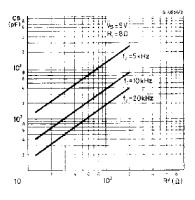


Figure 8. Frequency response

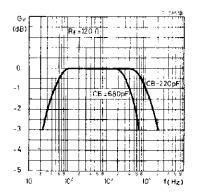


Figure 9. Harmonic distortion vs. frequency

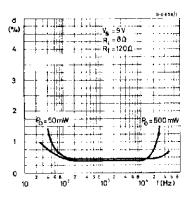


Figure 10. Supply voltage rejection (Fig. 2 circuit)

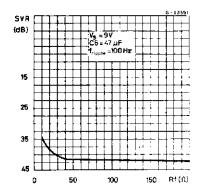
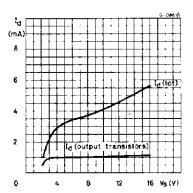
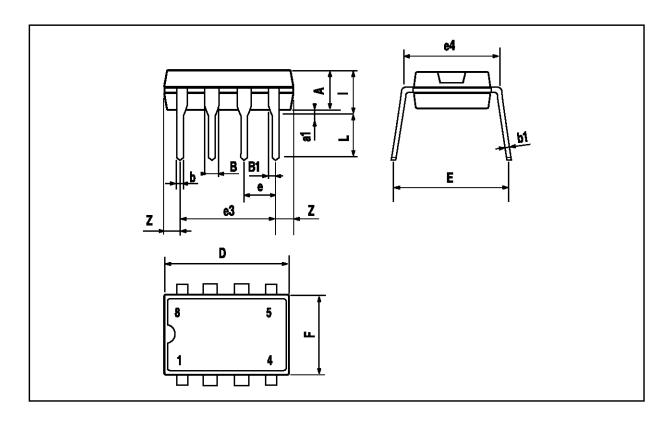


Figure 11. Quiescent current vs. supply voltage



## MINIDIP PACKAGE MECHANICAL DATA

DIM.	mm			inch			
Dilvi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А		3.32			0.131		
a1	0.51			0.020			
В	1.15		1.65	0.045		0.065	
b	0.356		0.55	0.014		0.022	
b1	0.204		0.304	0.008		0.012	
D			10.92			0.430	
Е	7.95		9.75	0.313		0.384	
е		2.54			0.100		
e3		7.62			0.300		
e4		7.62			0.300		
F			6.6			0.260	
I			5.08			0.200	
L	3.18		3.81	0.125		0.150	
Z			1.52			0.060	



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